

**Features**

- Ideally Suited for Automatic Insertion
- Low Current, Low Voltage
- Epitaxial Planar Die Construction
- Halogen Free. "Green" Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

**Maximum Ratings @ 25°C Unless Otherwise Specified**

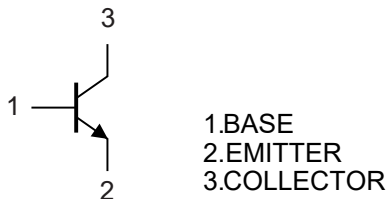
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 285°C/W Junction to Ambient<sup>(Note 2)</sup>
- Thermal Resistance: 215°C/W Junction to Soldering Point

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	75	V
Collector-Emitter Voltage	$V_{CEO}$	45	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Continuous Collector Current	$I_C$	800	mA
Peak Collector Current	$I_{CM}$	1000	mA
Continuous Base Current	$I_B$	100	mA
Peak Base Current	$I_{BM}$	200	mA
Power Dissipation	$T_S=79^\circ\text{C}$ $P_D$	330	mW

Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.  
2. Mounted on FR-4 Printed-Circuit Board.

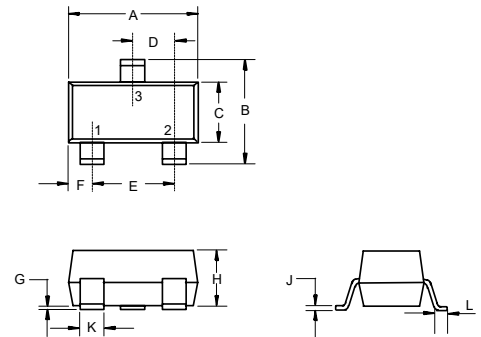
**Marking: EH**

**Internal Structure**



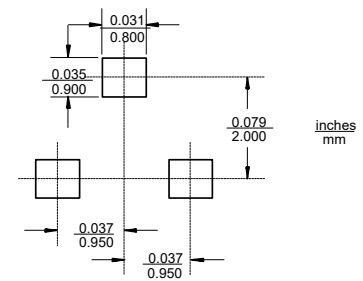
**NPN Small Signal Transistor**

**SOT-23**



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

**Suggested Solder Pad Layout**



**Electrical Characteristics @  $T_A=25^\circ\text{C}$  Unless Otherwise Specified**

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	75			V	$I_C=10\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	45			V	$I_C=10\text{mA}, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=10\mu\text{A}, I_C=0$
Collector-Base Cutoff Current	$I_{CBO}$			20	nA	$V_{CB}=45\text{V}, I_E=0$
				20	$\mu\text{A}$	$V_{CB}=45\text{V}, I_E=0, T_A=150^\circ\text{C}$
Emitter-Base Cutoff Current	$I_{EBO}$			20	nA	$V_{EB}=4\text{V}, I_C=0$
DC Current Gain	$h_{FE(1)}$	80				$V_{CE}=10\text{V}, I_C=100\mu\text{A}$
	$h_{FE(2)}$	180				$V_{CE}=1\text{V}, I_C=10\text{mA}$
	$h_{FE(3)}$	250		630		$V_{CE}=1\text{V}, I_C=100\text{mA}$
	$h_{FE(4)}$	100				$V_{CE}=2\text{V}, I_C=500\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3	V	$I_C=100\text{mA}, I_B=10\text{mA}$
				0.7	V	$I_C=500\text{mA}, I_B=50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.25	V	$I_C=100\text{mA}, I_B=10\text{mA}$
				2.0	V	$I_C=500\text{mA}, I_B=50\text{mA}$
Transition Frequency	$f_T$		100		MHz	$V_{CE}=10\text{V}, I_C=20\text{mA}, f=100\text{MHz}$
Collector-Base Capacitance	$C_{CB}$		6		pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Emitter-Base Capacitance	$C_{EB}$		60		pF	$V_{EB}=0.5\text{V}, f=1\text{MHz}$

**Curve Characteristics**

Fig. 1 - Static Characteristics

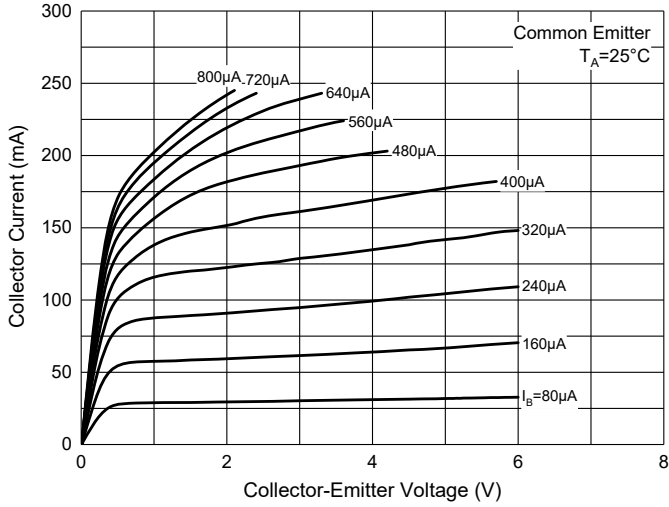


Fig. 2 - DC Current Gain Characteristics

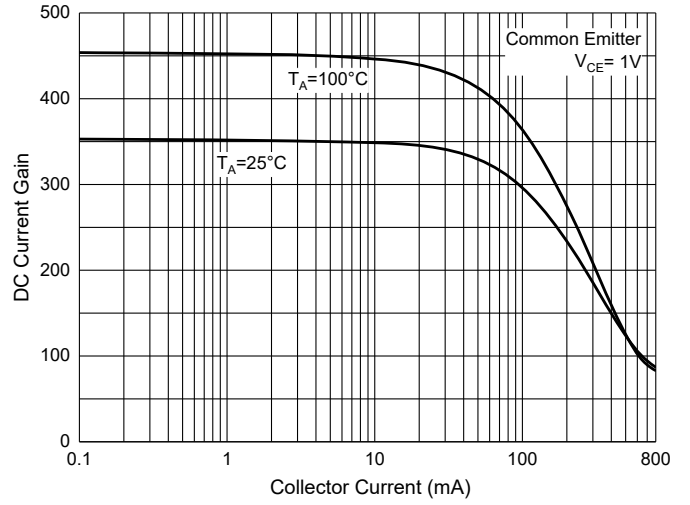


Fig. 3 - Base-Emitter Saturation Voltage Characteristics

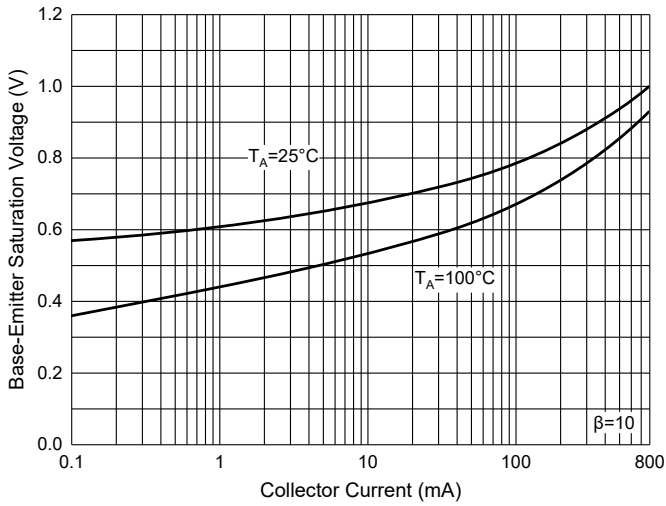


Fig. 4 - Collector-Emitter Saturation Voltage Characteristics

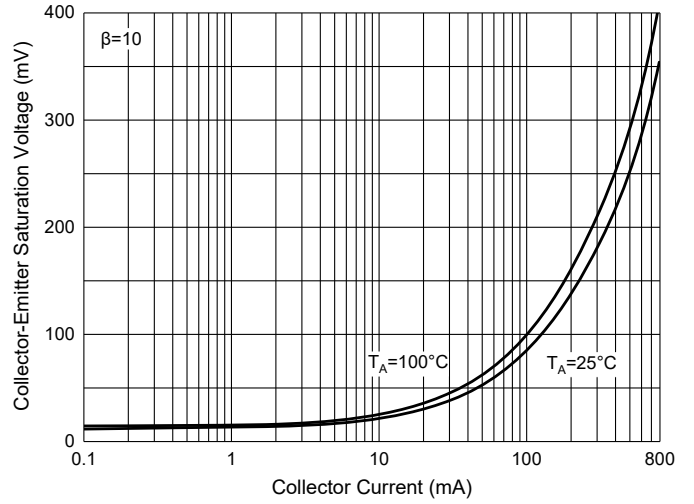


Fig. 5 - Collector Power Derating Curve

